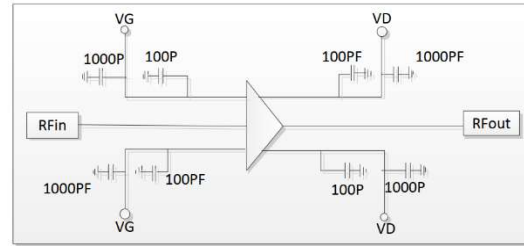


### Performance

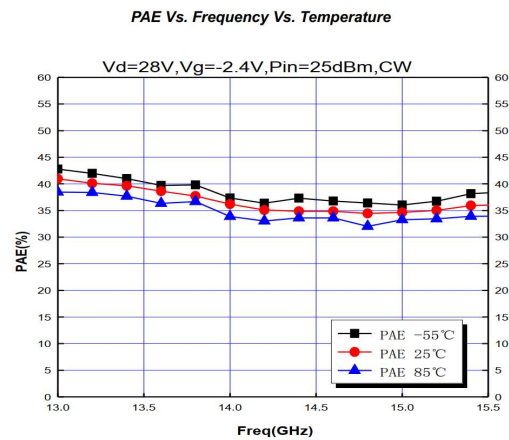
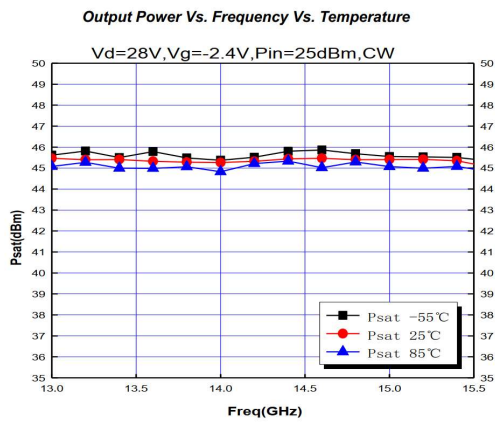
- Frequency: 13-15.5GHz
- Psat: 45dBm@28V
- Small Signal Gain: 23dB
- PAE: 33%
- Pin: 25dBm
- Bias: 28V, -2.4V (Typ.)
- Size: 18.03\*8.7mm\*2.24mm



### Electrical Specifications (Vd=28V, Vg=-2.4V, F: 13-15.5GHz, Pin=25dBm, CW)

Symbol	Parameter	Min	Typical	Max	Unit
G	Small Signal Gain	-	23	-	dB
Gp	Power Gain	-	20	-	dB
Pout	Saturated Power	-	45	-	dBm
PAE	Power Added Efficiency	-	33	-	%

### Test Curves

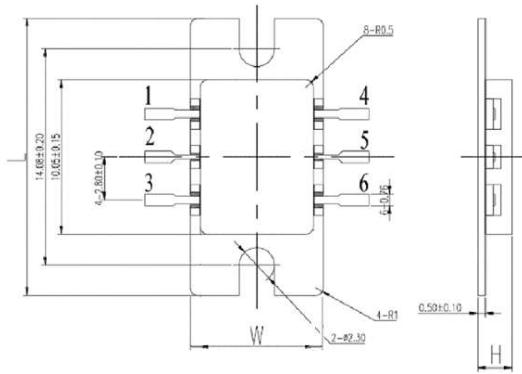


### Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	34V	
Vg	Gate Voltage	-10V	
Ig	Gate Current	50mA	
Pin	Input Power	30dBm	
VSWRout	Output VSWR	5:1	
Tch	Channel Temperature	220°C	
Tstg	Storage Temperature	-55~175°C	
ESD Level	Electro-static discharge Level	Class A	

Exceeding any one or combination of these limits may cause permanent damage.

Outline Size (See details on page 3 and 4)

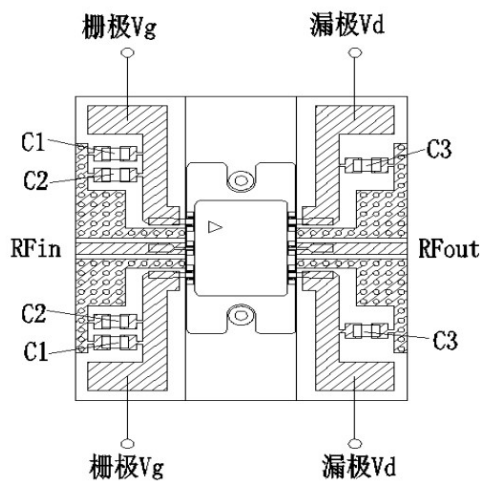


Symbol	Value		
	Min	Typical	Max
H	-	2.24	2.50
L	17.83	18.03	18.23
W	8.50	8.70	8.90

PIN Description

Pin No	Symbol	Description
1,3	Vg	Gate Voltage
2	RFin	Input, matched to 50Ω
4,6	Vd	Drain Voltage
5	RFout	Output, matched to 50Ω

Application Circuit



Symbol	Recommended Value
C1	10uF
C2	1uF
C3	1000pF

Bias-up Procedure

- 1 Set I<sub>g</sub> limit to 50mA
- 2 Apply -5V to V<sub>g</sub>
- 3 Apply +28V to V<sub>d</sub>, ensure I<sub>dq</sub> is approx. 0mA
- 4 Adjust V<sub>g</sub> to -2.4V typical
- 5 Turn on RF supply

Bias-down Procedure

- 1 Turn off RF supply
- 2 Reduce V<sub>g</sub> to -5.0V, ensure I<sub>dq</sub> is approx. 0mA
- 3 Set V<sub>d</sub> to 0V
- 4 Turn off V<sub>d</sub> supply
- 5 Turn off V<sub>g</sub> supply

